

**IN THE CLAIMS**

Please substitute claims 1-27 with the following:

1-26 (Cancelled).

27. (Currently Amended) A solid-state image sensor comprising:

unit pixels each having

a photoelectric conversion element for converting incident light into electric signal charge and then storing the signal charge obtained through such photoelectric conversion;

an amplifying element for amplifying the signal charge stored in said photoelectric conversion element into an electric signal; and

a reset element for resetting said signal charge, said reset element being a depletion transistor, ~~and~~

wherein the reset gate of said amplifying element outputs said electric signal of a reset charge level and a signal charge level for correlated double sampling depletion transistor is a transverse overflow barrier.